

**AMENDMENTS TO THE CLAIMS****Claims 1-13 (canceled)****14. (previously presented) A memory circuit, comprising:**

an array of single bit nonvolatile memory cells organized in columns, wherein each of the memory cells comprises a semiconductor substrate including a source, a drain, and a channel in-between the source and the drain; and a control gate that comprises a gate electrode and a dielectric stack, the gate electrode being separated from the channel by the dielectric stack, the dielectric stack comprising at least one charge storage dielectric layer, wherein:

adjacent memory cells in each column of the memory circuit have one of their sources and their drains in common;

the sources of the memory cells in each column of the memory circuit are coupled with the same bitline, the bitline running parallel with the column;

the drains of the memory cells in each column of the memory circuit are coupled with a respective program line, the program line running perpendicular to the column; and

the gates of the memory cells in each column of the memory circuit are coupled with a respective word line, the word line running perpendicular to the column, wherein programming a memory cell of the memory circuit comprises:

applying electrical ground to a first bitline;

applying a first voltage having a first polarity to a wordline;

applying a second voltage of the first polarity to a program line;

applying a third voltage, having a second polarity opposite to the first polarity to the semiconductor substrate; and

applying a fourth voltage of the first polarity to all other bitlines of the memory circuit.

Claim 15 (canceled)

Claim 16 (previously presented) The memory circuit of claim 14, wherein absolute values of each of the first, second and third voltages are 5 V or less, and an absolute value of the fourth voltage is 2 V or less.